

DESCRIPTION

Mitsubishi 2SA1947 is a resin sealed silicon PNP epitaxial type transistor. It is designed with high collector current and 2 to 3.5W low frequency power amplify. Complementary with 2SC5214.

FEATURE

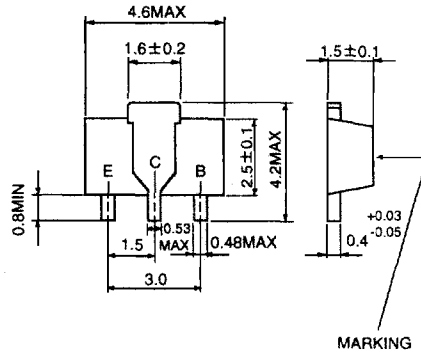
- High fr $f_T=100\text{MHz typ}$
- Excellent linearity of DC forward current gain
- High collector current $I_{CM}=1.5A$
- Small package for mounting

APPLICATION

Radio, tape recorder, small type stereo, etc.
Low frequency power amplify circuit with 2 to 3.5W output.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

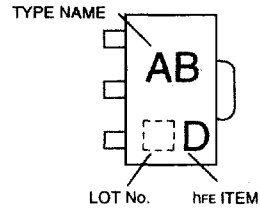
- E : EMITTER
- C : COLLECTOR
- B : BASE
- EIAJ : SC-62
- JEDEC : -

Note)
The dimension without tolerance represent central value.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Ratings	Unit
V_{CB0}	Collector to Base voltage	-30	V
V_{EB0}	Emitter to Base voltage	-4	V
V_{CE0}	Collector to Emitter voltage	-25	V
I_{CM}	Peak collector current	-1.5	A
I_C	Collector current	-1	A
P_C	Collector dissipation($T_a=25^\circ\text{C}$)	500	mW
T_j	Junction temperature	+150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to +150	$^\circ\text{C}$

MARKING



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=-10\mu A, I_E=0$	-30			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=-10\mu A, I_C=0$	-4			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=-100\mu A, R_{BE}=\infty$	-25			V
I_{CBO}	Collector cut off current	$V_{CB}=-25V, I_E=0$			-1	μA
I_{EBO}	Emitter cut off current	$V_{BE}=-2V, I_C=0$			-1	μA
hFE *	DC forward current gain	$V_{CE}=-1V, I_C=-500mA$	55		300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=-500mA, I_B=-25mA$			-0.5	V
fr	Gain band width product	$V_{CE}=-6V, I_E=10mA$		100		MHz

* : It shows hFE classification in right table.

Marking	ABC	ABD	ABE
hFE	55 to 110	90 to 180	150 to 300

FOR LOW FREQUENCY POWER AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS

